United States Bankruptcy Court Northern District of California

In re

.

Silicon Genesis Corporation

Debtor

Case No. 15-50525 MEH

11 Chapter_

SUMMARY OF SCHEDULES

Indicate as to each schedule whether that schedule is attached and state the number of pages in each. Report the totals from Schedules A, B, D, E, F, I, and J in the boxes provided. Add the amounts from Schedules A and B to determine the total amount of the debtor's assets. Add the amounts of all claims from Schedules D, E, and F to determine the total amount of the debtor's liabilities. Individual debtors must also complete the "Statistical Summary of Certain Liabilities and Related Data" if they file a case under chapter 7, 11, or 13.

NAME OF SCHEDULE	ATTACHED (YES/NO)	NO. OF SHEETS	ASSETS	LIABILITIES	OTHER
A - Real Property	Yes	1	0.00		
B - Personal Property	Yes	10	16,559,802.83		
C - Property Claimed as Exempt	No	0			
D - Creditors Holding Secured Claims	Yes	1		7,688,182.09	
E - Creditors Holding Unsecured Priority Claims (Total of Claims on Schedule E)	Yes	2		186.00	
F - Creditors Holding Unsecured Nonpriority Claims	Yes	6		262,675.10	
G - Executory Contracts and Unexpired Leases	Yes	1			
H - Codebtors	Yes	1			
I - Current Income of Individual Debtor(s)	No	0			N/A
J - Current Expenditures of Individual Debtor(s)	No	0			N/A
Total Number of Sheets of ALL Schedu	ıles	22			
	Te	otal Assets	16,559,802.83		
			Total Liabilities	7,951,043.19	



United States Bankruptcy Court Northern District of California

In re

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Silicon Genesis Corporation

Debtor

Case No. _____15-50525 MEH

11 Chapter_

STATISTICAL SUMMARY OF CERTAIN LIABILITIES AND RELATED DATA (28 U.S.C. § 159)

If you are an individual debtor whose debts are primarily consumer debts, as defined in § 101(8) of the Bankruptcy Code (11 U.S.C.§ 101(8)), filing a case under chapter 7, 11 or 13, you must report all information requested below.

Check this box if you are an individual debtor whose debts are NOT primarily consumer debts. You are not required to report any information here.

This information is for statistical purposes only under 28 U.S.C. § 159.

Summarize the following types of liabilities, as reported in the Schedules, and total them.

Type of Liability	Amount
Domestic Support Obligations (from Schedule E)	
Taxes and Certain Other Debts Owed to Governmental Units (from Schedule E)	
Claims for Death or Personal Injury While Debtor Was Intoxicated (from Schedule E) (whether disputed or undisputed)	
Student Loan Obligations (from Schedule F)	
Domestic Support, Separation Agreement, and Divorce Decree Obligations Not Reported on Schedule E	
Obligations to Pension or Profit-Sharing, and Other Similar Obligations (from Schedule F)	
TOTAL	

State the following:

Average Income (from Schedule I, Line 12)	
Average Expenses (from Schedule J, Line 22)	
Current Monthly Income (from Form 22A-1 Line 11; OR, Form 22B Line 14; OR, Form 22C-1 Line 14)	

State the following:

1. Total from Schedule D, "UNSECURED PORTION, IF ANY" column	
2. Total from Schedule E, "AMOUNT ENTITLED TO PRIORITY" column	
3. Total from Schedule E, "AMOUNT NOT ENTITLED TO PRIORITY, IF ANY" column	
4. Total from Schedule F	
5. Total of non-priority unsecured debt (sum of 1, 3, and 4)	



Debtor

SCHEDULE A - REAL PROPERTY

Except as directed below, list all real property in which the debtor has any legal, equitable, or future interest, including all property owned as a cotenant, community property, or in which the debtor has a life estate. Include any property in which the debtor holds rights and powers exercisable for the debtor's own benefit. If the debtor is married, state whether husband, wife, both, or the marital community own the property by placing an "H," "W," "J," or "C" in the column labeled "Husband, Wife, Joint, or Community." If the debtor holds no interest in real property, write "None" under "Description and Location of Property."

Do not include interests in executory contracts and unexpired leases on this schedule. List them in Schedule G - Executory Contracts and Unexpired Leases.

If an entity claims to have a lien or hold a secured interest in any property, state the amount of the secured claim. See Schedule D. If no entity claims to hold a secured interest in the property, write "None" in the column labeled "Amount of Secured Claim." If the debtor is an individual or if a joint petition is filed, state the amount of any exemption claimed in the property only in Schedule C - Property Claimed as Exempt.

Description and Location of Property	Nature of Debtor's Interest in Property	Husband, Wife, Joint, or Community	Current Value of Debtor's Interest in Property, without Deducting any Secured Claim or Exemption	Amount of Secured Claim
--------------------------------------	--	---	--	----------------------------

None

Sub-Total > 0.0	0 (Total of this page)
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0.00

Total >

0 continuation sheets attached to the Schedule of Real Property

Case: 15-50525 Doc# 8 Filed: 02/18/15 Entered: 02/18/15 17:43:37 Software Copyright (c) 1996-2014 - Best Case, LLC - www.bestcase.com

(Report also on Summary of Schedules) htered: 02/18/15 17:43:37 Page 3 of 25

Case No. 15-50525 MEH

Debtor

SCHEDULE B - PERSONAL PROPERTY

Except as directed below, list all personal property of the debtor of whatever kind. If the debtor has no property in one or more of the categories, place an "x" in the appropriate position in the column labeled "None." If additional space is needed in any category, attach a separate sheet properly identified with the case name, case number, and the number of the category. If the debtor is married, state whether husband, wife, both, or the marital community own the property by placing an "H," "W," "J," or "C" in the column labeled "Husband, Wife, Joint, or Community." If the debtor is an individual or a joint petition is filed, state the amount of any exemptions claimed only in Schedule C - Property Claimed as Exempt.

Do not list interests in executory contracts and unexpired leases on this schedule. List them in Schedule G - Executory Contracts and Unexpired Leases.

If the property is being held for the debtor by someone else, state that person's name and address under "Description and Location of Property." If the property is being held for a minor child, simply state the child's initials and the name and address of the child's parent or guardian, such as "A.B., a minor child, by John Doe, guardian." Do not disclose the child's name. See, 11 U.S.C. §112 and Fed. R. Bankr. P. 1007(m).

	Type of Property	N O N E Description and Location of Property	Husband, Wife, Joint, or Community	Current Value of Debtor's Interest in Property, without Deducting any Secured Claim or Exemption
1.	Cash on hand	x		
2.	Checking, savings or other financial accounts, certificates of deposit, or	Operating Account, Silicon Valley Bank	-	147,930.00
	shares in banks, savings and loan, thrift, building and loan, and homestead associations, or credit unions, brokerage houses, or	Payroll Account, Silicon Valley Bank	-	0.00
	cooperatives.	Sweep Account, Silicon Valley Bank	-	0.00
3.	Security deposits with public utilities, telephone companies, landlords, and others.	x		
4.	Household goods and furnishings, including audio, video, and computer equipment.	x		
5.	Books, pictures and other art objects, antiques, stamp, coin, record, tape, compact disc, and other collections or collectibles.	x		
6.	Wearing apparel.	x		
7.	Furs and jewelry.	x		
8.	Firearms and sports, photographic, and other hobby equipment.	X		
9.	Interests in insurance policies. Name insurance company of each policy and itemize surrender or refund value of each.	X		
10.	Annuities. Itemize and name each issuer.	x		

5 continuation sheets attached to the Schedule of Personal Property

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Case No. 15-50525 MEH

Debtor

SCHEDULE B - PERSONAL PROPERTY

(Continuation Sheet)

	Type of Property	N O N E	Description and Location of Property	Husband, Wife, Joint, or Community	Current Value of Debtor's Interest in Property, without Deducting any Secured Claim or Exemption
11.	Interests in an education IRA as defined in 26 U.S.C. § 530(b)(1) or under a qualified State tuition plan as defined in 26 U.S.C. § 529(b)(1). Give particulars. (File separately the record(s) of any such interest(s). 11 U.S.C. § 521(c).)	х			
12.	Interests in IRA, ERISA, Keogh, or other pension or profit sharing plans. Give particulars.	X			
13.	Stock and interests in incorporated and unincorporated businesses. Itemize.	Х			
14.	Interests in partnerships or joint ventures. Itemize.	Х			
15.	Government and corporate bonds and other negotiable and nonnegotiable instruments.	x			
16.	Accounts receivable.		liquidated payments due under license agreements	-	1,516,060.50
17.	Alimony, maintenance, support, and property settlements to which the debtor is or may be entitled. Give particulars.	х			
18.	Other liquidated debts owed to debtor including tax refunds. Give particulars.		Judgment against Legalforce, Inc., and Raj Abhyanker, P.C.	-	462,812.33
19.	Equitable or future interests, life estates, and rights or powers exercisable for the benefit of the debtor other than those listed in Schedule A - Real Property.	X			
20.	Contingent and noncontingent interests in estate of a decedent, death benefit plan, life insurance policy, or trust.	X			
21.	Other contingent and unliquidated claims of every nature, including tax refunds, counterclaims of the debtor, and rights to setoff claims. Give estimated value of each.		patent infringement claims	-	Unknown
			(Total	Sub-Tot of this page)	al > 1,978,872.83

Sheet <u>1</u> of <u>5</u> continuation sheets attached to the Schedule of Personal Property

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Debtor

SCHEDULE B - PERSONAL PROPERTY

(Continuation Sheet)

	Type of Property	N O Description and Location of Property E	Husband, Wife, Joint, or Community	Current Value of Debtor's Interest in Property, without Deducting any Secured Claim or Exemption
22.	Patents, copyrights, and other intellectual property. Give particulars.	See Attachment B.22	-	Unknown
23.	Licenses, franchises, and other general intangibles. Give	NPV of projected royalties due under license agreement with Shin-Etsu Chemical Co., Ltd.	-	7,500,000.00
	particulars.	NPV of projected royalties due under license agreement with EV Group E. Thallner GmbH	-	1,000,000.00
		NPV of projected royalties due under license agreements with Applied Materials and QMAT, Inc.	-	Unknown
24.	Customer lists or other compilations containing personally identifiable information (as defined in 11 U.S.C. § 101(41A)) provided to the debtor by individuals in connection with obtaining a product or service from the debtor primarily for personal, family, or household purposes.	X		
25.	Automobiles, trucks, trailers, and other vehicles and accessories.	X		
26.	Boats, motors, and accessories.	X		
27.	Aircraft and accessories.	X		
28.	Office equipment, furnishings, and supplies.	x		
29.	Machinery, fixtures, equipment, and supplies used in business.	Cryo pump Cyclotron Cyro pump parts	-	5,000.00
		Edwards QDP-40 dry pump	-	1,000.00
		Korvis Asyst Robot spare robot for spa tool	-	10,000.00
		Power supply HV stack - for P-III	-	500.00
		Manual PA Manual plasma activation tool	-	200,000.00
		Robot isoports FOUP Openers	-	50,000.00

(Total of this page)

8,766,500.00

Sub-Total >

Sheet <u>2</u> of <u>5</u> continuation sheets attached to the Schedule of Personal Property

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Debtor

SCHEDULE B - PERSONAL PROPERTY

(Continuation Sheet)

Type of Property	N O Description and Location of Property E	Husband, Wife, Joint, or Community	Current Value of Debtor's Interest in Property, without Deducting any Secured Claim or Exemption
	rT-CCP room temperature cleave tool	-	1,000,000.00
	rT-CCP room temperature cleave tool - used	-	250,000.00
	SPA automated plasma activation tool	-	1,000,000.00
	Allwin Gen3+ Rapid Thermal Oven	-	100,000.00
	RD-4 accelerator 1.1 MeV implant system	-	2,500,000.00
	Allwin Gen2 Rapid Thermal Oven	-	10,000.00
	Allwin Gen3 Rapid Thermal Oven	-	75,000.00
	Ansys FEA Software finite element analysis	-	5,000.00
	Bede-1 XRD xray diffraction tool	-	10,000.00
	Blue M#1 Blue M-Oven	-	5,000.00
	IDE AFM Atomic Force Microscope	-	50,000.00
	Lab Tables and Benches tables and benches	-	1,000.00
	Manual PA R&D tool	-	5,000.00
	Nikon Microscope microscope	-	5,000.00
	Office Furniture FH and PO offices	-	1,000.00
	Olympus Microscope		5,000.00

Sheet <u>3</u> of <u>5</u> continuation sheets attached to the Schedule of Personal Property Case: 15-50525 Doc# 8 Filed: 02/18/15 Entered: 02/18/15 17:43:37 Page 7 of 25 Software Copyright (c) 1996-2014 - Best Case, LLC - www.bestcase.com

(Total of this page)

Sub-Total >

5,022,000.00

Debtor

SCHEDULE B - PERSONAL PROPERTY

(Continuation Sheet)

Type of Property	N O Description and Location of Property E	Husband, Wife, Joint, or Community	Current Value of Debtor's Interest in Property, without Deducting any Secured Claim or Exemption
	P-III Implanter Plasma implant tool	-	200,000.00
	QA Wet Bench Solven clean sink	-	15,000.00
	Rofin-Sinar Diode Laser Laser	-	25,000.00
	TC Bonder Manual bonding tool	-	10,000.00
	Toshiba 4520c Copier copy machine	-	10,000.00
	Universal Wet Bench Acid clean sink	-	25,000.00
	Cyclotron 4.0 MeV Cyclotron Implanter	-	150,000.00
	Delage Landon Forklift forklift	-	2,500.00
	Dynamitron End Station Dynamitron End Station	-	100,000.00
	Heidehan spectrometer	-	1,000.00
	Sinton BCT-300 Tester Solar wafer lifetime tool	-	20,000.00
	Summitt air compressor air compressor system/vac	-	1,000.00
	GE DI-H20 - 1500-gal deionized water system	-	20,000.00
	YORK Chiller water chiller	-	15,000.00
	Carrier Chiller water chiller	-	5,000.00
	Kobelco CDA Tower/60hp clean dry air	-	25,000.00

Sheet <u>4</u> of <u>5</u> continuation sheets attached to the Schedule of Personal Property Case: 15-50525 Doc# 8 Filed: 02/18/15 Entered: 02/18/15 17:43:37 Page 8 of 25 Software Copyright (c) 1996-2014 - Best Case, LLC - www.bestcase.com

(Total of this page)

Sub-Total >

624,500.00

Case No. 15-50525 MEH

Debtor

SCHEDULE B - PERSONAL PROPERTY (Continuation Sheet)

Type of Property	N O N E Description and Location of Property E	Husband, Wife, Joint, or Community	Current Value of Debtor's Interest in Property, without Deducting any Secured Claim or Exemption
	Acid cabinets hazardous chemical storage	-	5,000.00
	Clean Room Components soft wall clean room/hepa filters	-	15,000.00
30. Inventory.	x		
31. Animals.	x		
 Crops - growing or harvested. Give particulars. 	x		
 Farming equipment and implements. 	x		
34. Farm supplies, chemicals, and feed.	x		
35. Other personal property of any kind not already listed. Itemize.	x		

	Sub-Total >	20,000.00
	(Total of this page)	
Sheet 5 of 5 continuation sheets attached	Total >	16,559,802.83
to the Schedule of Personal Property	(Report also on Su	ummary of Schedules)
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ATTACHMENT B.22

PHDATA 5232130_1 Case: 15-50525 Doc# 8 Filed: 02/18/15 Entered: 02/18/15 17:43:37 Page 10 of

SiGen Patent Portfolio

Patent Number	Country	Filed	Issued	Title	
US20130209740A1 Feb 13,2012 Sapphire continuation patent (confidential)	USA USA	2/13/2013	-	Apparatus and Method of Cleaving Thin Layer from Bulk Material Apparatus and Method of Cleaving Thin Layer from Bulk Material	

Bet2307 EPO 07/21958 04/212004 System For The Plasma Treatmont Of Large Area Substrates 1199499 Germany 4/220200 04/112000 Surface Finishing of OSI Substrates Using an EPI Process 1199499 France 04/202000 12/122000 Surface Finishing of SOI Substrates Using an EPI Process 240940 UK 11003/2003 Berlazcott Method for Treating Semiconduct Material 240940 UK 11003/2003 Berlazcott Method for Treating Semiconduct Material 240940 USA 02/19/1986 111/22000 Farama Treatment Appartus for Large Area Substrates 240940 USA 02/19/1986 101/12002 Controlled Cleavage Process and Device for Patterned Films 24017 USA 02/19/1986 101/12002 Controlled Cleavage Process Using Pressured Filud 013547 USA 02/19/1986 101/12002 Controlled Cleavage Process Using Pressured Filud 013547 USA 02/19/1989 101/12002 Controlled Cleavage Process Using Pressured Filud 013547 USA 06/03/1989 01/12/2002 Controlled Cleavage Process Using Resure2ed	
119499 France 04/20/2001 Surface Finishing of SOI Substrates Using an EPI Process 119499 EPO 04/20/2003 06/18/2003 Surface Finishing of SOI Substrates Using an EPI Process 119499 EPO 04/20/2003 06/18/2001 Nethod for Treating Semicoductor Material 119490 USA 07/21/19/8 11/14/2000 System for the Pasma Treatment Apparatus for Large Area Substrates 534012 USA 02/17/19/8 01/04/2000 Trumbing Barrel Pasma Treatment Apparatus for Large Area Substrates 534020 USA 02/17/19/88 01/04/2000 Controlled Cleavage Process and Device for Patterned Films 534207 USA 02/21/19/88 11/14/2000 Controlled Cleavage Process USA 601357 USA 02/19/19/88 11/13/20189 Controlled Cleaving Process USA 6013567 USA 05/07/19/99 01/11/2000 Sufface Finishing Pressurized Field 601357 USA 05/07/19/98 01/22/2000 Controlled Cleaving Process USA 603357 USA 06/07/19/98 00/27/20/00 Preforated Site of Plasma Immersion	
194949 EPO 04/20/2000 05/06/2003 Surface Finishing of SOI Substrates Using an EP Process 208340 UK 1003/2003 09/12/2000 Plasma Treatment Apparatus for Large Area Substrates 132217 Japan 07/2/1996 11/14/2000 System for the Plasma Treatment of Large Area Substrates 503811 USA 02/19/1986 10/14/2000 System for the Plasma Treatment of Large Area Substrates 503671 USA 02/19/1986 10/14/2000 Controlled Cleavage Process Using Pressurized Fluid 601579 USA 02/19/1998 10/10/2002 Controlled Cleavage Process Using Pressurized Fluid 6013563 USA 02/19/1998 10/10/2002 Controlled Cleaving Process 6013567 USA 06/07/1996 09/12/2003 Station Process 10/14/14/2004 6013573 USA 06/07/1996 09/12/2003 Station Process 10/14/14/2004 6013563 USA 06/07/1996 09/12/2004 Febrinating Technique for Silicon-on-insulator Wafers 6013563 USA 06/07/1996 09/14/2004 Febrinating Techning technique for Silicon-on	
240940 UK 1003/2003 09/18/2001 Method for Treating Semant Apparatus for Large Area Substrates 242817 Japan 077/19/1905 11/14/2000 Plasma Treatment Apparatus for Large Area Substrates 5454012 USA 02/11/1996 01/14/2000 Turning Barrel Plasma Treatment of Large Area Substrates 5454012 USA 02/11/1996 01/14/2000 Controlled Cleavage Process and Device for Patterned Films 5994307 USA 02/11/1998 05/12/2001 Controlled Cleavage Process Bigg Process 6013567 USA 02/11/1998 10/22/000 Reusable Substrate for Thin Film Separation 6013567 USA 02/11/1998 10/22/000 Reusable Substrate for Thin Film Separation 6013567 USA 02/11/1998 01/22/000 Reusable Substrate Fluid 6013567 USA 06/03/1998 11/22/000 Reusable Substrate Fluid 6013567 USA 06/03/1998 10/22/000 Petroated Shield for Plasma Immersion Ion Implantation 64/2324 USA 02/11/1998 09/14/2001 Reusaple Substrate 61/3735 </td <td></td>	
122217 Japan 12/2/2000 Plasma Treatment Appareus for Large Area Substrates 553811 USA 07/2/1996 11/4/2000 System for the Plasma Treatment of Large Area Substrates 594502 USA 02/17/1998 10/4/2000 Tumbing Barrel Plasma Processor 594502 USA 02/16/1998 10/12/002 Controlled Cleavage Process Using Pressurized Fluid 601557 USA 02/16/1998 10/12/002 Controlled Cleavage Process Using Pressurized Fluid 6013563 USA 02/16/1998 10/10/1099 Cleavage Process Using Pressurized Fluid 6013567 USA 05/05/1998 10/11/2000 Controlled Cleavage Process Using Pressurized Fluid 603367 USA 02/16/1998 10/12/000 Controlled Cleavage Process 10/14/000 603367 USA 02/16/1998 09/14/2001 Seltening Technique for Multilayered Substrates 603367 USA 02/16/1998 09/14/2001 Retaining Technique for for Plasma Immersion Ion Implantation 603369 USA 02/16/1998 09/14/2004 Renovable Liner Design for Plasma Immersion Ion Implantation	Implanter
533311 USA 07/19/1995 11/14/2000 System for the Plasma Treatment of Large Area Substrates 594512 USA 02/19/1998 01/01/2002 Controlled Cleavage Process and Device for Patterned Films 5985742 USA 02/19/1998 01/01/2002 Controlled Cleavage Process and Device for Patterned Films 5985742 USA 02/19/1998 10/01/2002 Controlled Cleavage Process Using Pressurized Fluid 6013567 USA 02/19/1998 11/03/1090 Controlled Cleavage Process 6013567 USA 02/19/1998 10/12/2000 Caronal Device Frances Study Pressurized Fluid 603357 USA 08/01/1998 01/12/2000 Controlled Cleavage Process More Study Pressurized Fluid 603357 USA 02/19/1998 01/12/2002 Flanaruing Technique for Silicon-Norinseulator Wafers 603359 USA 02/01/1998 03/02/2002 Paranizing Technique for Multilayerd Substrates 613373 USA 03/01/1998 06/22/2003 Nevel Distributed System and Code for Control and Automation of Plasma Immersion for Inplanation 6146979 USA 02/19/1998	Implanter
5145012 USA 02/17/1968 01/04/2000 "umbiing Barrel Param Processor 5385742 USA 02/19/1968 01/01/2002 Controlled Cleavage Process Using Pressurized Fluid 6010579 USA 02/19/1968 10/01/2001 Controlled Cleavage Process Using Pressurized Fluid 6013563 USA 02/19/1969 11/11/1969 Controlled Cleavage Process Using Pressurized Fluid 6013567 USA 05/09/1999 01/11/2000 Controlled Cleavage Process Using Pressurized Fluid 6013574 USA 02/19/1998 03/07/2000 Perforated Shield for Plasma Immersion Ion Implantation 6033574 USA 06/03/1998 03/07/2000 Perforated Shield for Plasma Immersion Ion Implantation 603354 USA 06/03/1998 01/12/2000 Perforated Shield for Plasma Immersion Ion Implantation 613535 USA 06/03/1998 01/22/2000 Removable Liner Design for Plasma Immersion Ion Implantation 613536 USA 02/19/1998 03/25/2008 Fressurized Microbubbe Thin Flim Separation Process Using a Reusable Substrate 613524 USA 02/19/1998 03/25/2008 <	
985742 USA 02/19/1988 01/01/2002 Controlled Cleavage Process and Device for Patterned Films 5994207 USA 02/19/1989 12/05/2001 Controlled Cleavage Process Using Pressurized Fluid 6013567 USA 02/19/1989 11/30/1990 Controlled Cleavage Process Usa 6013567 USA 05/05/1990 01/11/2000 Controlled Cleavage Process Usa 6013567 USA 05/05/1990 01/12/2000 Controlled Cleavage Process Usa 6033974 USA 06/01/1990 00/12/2000 Retrolated Cleavage Process Usa 05/01/1990 6048411 USA 02/19/1998 09/04/2001 Gettering Technique for Multisyered Substrates 601323 USA 02/19/1998 09/04/2001 Gettering Technique for Multisyered Substrates 6113735 USA 02/19/1998 09/04/2002 Removable Liner Design for Plasma Immersion Ion Implantation 6126660 USA 02/19/1998 03/25/2002 Resuizing Pressuized Fluid 613542 USA 02/19/1998 03/22/2002 Resuising Pressuized Fluid<	
S994207 USA 02/19/1988 06/12/2001 Controlled Cleavage Process Using Pressurized Fluid 6013563 USA 02/19/1988 11/03/1999 Controlled Cleaving Process 6013567 USA 05/05/1999 Ontrolled Cleaving Process Usa 601357 USA 05/05/1999 Ontrolled Cleaving Process Usa 6033974 USA 02/19/1988 00/17/2000 Periorated Shield for Press Environmentation 604411 USA 02/19/1989 09/18/2001 Gettering Technique for Silicon-on-Insulator Wafers 6051072 USA 06/03/1986 11/26/2002 Perinatic for Multilayered Substrates 6133735 USA 06/03/1986 03/27/2000 Perinatic for Multilayered Substrates 613524 USA 02/19/1989 03/27/2000 Removable Liner Design for Plasma Immersion Ion Implantation 613563 USA 02/19/1989 03/25/2008 Fruster To Method Using Pressurized Fluid 613554 USA 02/19/1989 03/25/2008 Controlled Cleavage Thin Film Separation Process Using a Reusable Substrate 613552 <	Implanter
BitISTP USA 02/19/1988 12/05/2000 Reusable Substrate for Thin Film Separation 6013563 UISA 02/19/1988 11/01/1900 Controlled Cleaving Process USA 05/05/1989 01/11/2000 Controlled Cleaving Process USA 06/05/1989 01/11/2000 Controlled Cleaving Process USA 06/07/1989	Implanter
BitsBits USA 02191998 11/301999 Controlled Cleavage Process Using Pressurized Fluid 6033974 USA 08/001999 01/11/2000 Controlled Cleavage Process Using Pressurized Fluid 6033974 USA 08/001999 01/12/2003 Method for Controlled Cleavage Process 6048411 USA 06/031988 03/07/2000 Performated Shiled for Plasma Immersion Ion Implantation 6083324 USA 06/031988 03/07/2000 Performing to Process 6103599 USA 06/031988 03/07/2000 Performing to Process Performant Immersion Ion Implantation 6126600 USA 02/19/1998 03/22/2003 Nevel Distributed System and Code for Control and Automation of Plasma Immersion Ion Implantation 6126600 USA 02/19/1998 03/22/2003 Pressurized Microbuble Thin Film Separation Process Using a Reusable Substrate 6135324 USA 02/19/1998 02/13/2001 Silicon-on-Silicon Water Bonding Process Using a Reusable Substrate 615925 USA 02/19/1998 02/13/2001 Silicon-on-Silicon Water Bonding Process Using a Reusable Substrate 615926 USA	Implanter
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6287941 USA 09/20/1999 05/10/2005 Surface Finishing of SOI Substrates Using an EPI Process	
6290804 USA 02/19/1998 08/15/2000 Controlled Cleavage Process Using Patterning	
6291313 USA 05/18/1999 08/07/2001 Method and Device for Controlled Cleaving Process	
6291314 USA 06/17/1999 04/18/2000 Controlled Cleavage Process and Device for Patterned Films Using a Release Layer	
C291326 USA 06/17/1999 04/17/2001 Pre-Semiconductor Process Implant and Post-Process Film Separation	
C224814 USA 08/24/1999 09/19/2000 Cleaved Silicon Thin Film With Rough Surface	
6300227 USA 12/01/1998 02/13/2001 Enhanced Plasma Mode, Method, and System for Plasma Immersion Ion Implantation	
OSA T2/07/35/0 OF/32/07 Enhanced Hashing Week, Weaked, and System for Hashing Hinderform Internation (International Internation) 6321134 USA 07/28/1998 05/08/2001 Cluster Tool System Software Using Plasma Immersion Ion Implantation	
6335264 USA 09/15/2000 06/06/2006 Controlled Cleavage Thin Film Separation Process Using a Reusable Substrate	
6338313 USA 04/24/1998 05/27/2008 System for the Plasma Treatment of Large Area Substrates	
6391740 USA 04/28/1999 10/24/2012 Generic Layer Transfer Methodology by Controlled Cleavage Process Method and System for Generating a Plurality of Donor Wafers and Handle Wafers Prior	o an Order
6448152 USA 07/16/2001 04/29/2003 Being Placed by a Customer	
0448132 05A 07/10/2001 04/20/2003 Deling Flaced by a Costonier 6455399 USA 03/14/2001 05/21/2002 Smoothing Method for Cleaved Films Made Using Thermal Treatment	
6458672 USA 11/02/2000 08/14/2001 Controlled Cleaved Tims Made Using Thermal Treament	
6486041 USA 02/20/2001 04/24/2001 Method and Device for Controlled Cleaving Process	
6489241 USA 09/17/1999 09/05/2000 Surfacing Finishing of SOI Substrates Using an EPI Process	
6500732 USA 07/27/2000 09/18/2001 Cleaving Process to Fabricate Multilayered Substrates Using Low Implantation Doses	
6511899 USA 05/06/1999 02/06/2001 Controlled Cleavage Process Using Pressurized Fluid	
6513564 USA 03/14/2001 06/19/2001 Nozzle for Cleaving Substrates	
6514838 USA 06/27/2001 09/18/2001 Method for Non Mass Selected Ion Implant Profile Control	
6528391 USA 05/21/1999 10/09/2001 Controlled Cleavage Process and Device for Patterned Films	
6534381 USA 01/04/2000 04/10/2001 Method for Fabricating Multi-Layered Substrates	
6544862 USA 01/14/2000 03/18/2003 Particle Distribution Method and Resulting Structure for a Layer Transfer Process	
6548382 USA 08/04/2000 01/09/2001 Gettering Technique for Wafers Made Using a Controlled Cleaving Process	

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SiGen Patent Portfolio

Patent Number	Country	Filed	Issued	Title
6554046	USA	11/27/2000		Substrate Cleaving Tool and Method
6558802 6582999	USA USA	02/29/2000 04/05/2001		Silicon-On-Silicon Hybrid Wafer Assembly Controlled Cleavage Process Using Pressurized Fluid
6632324	USA	04/03/2001		System for the Plasma Treatement of Large Area Substrates
6632724	USA	01/13/2000		Controlled Cleaving Process
6645828	USA	09/08/2000	08/07/2007	In Situ Plasma Wafer Bonding Method
6780759	USA	10/01/2001		Method for Multi-Frequency Bonding
6790747	USA	10/09/2002		Method and Device for Controlled Cleaving Process
6881644 6890838	USA	05/17/2002 03/26/2003		Smoothing Method for Cleaved Films Made Using a Release Layer Gettering Technique for Wafers Made Using a Controlled Cleaving Process
6908832	USA	10/06/2003		In Situ Plasma Wafer Bonding Method
6969668	USA	11/08/2000		Treatment Method of Film Quality for the Manufacture of Substrates
7056808	USA	11/20/2002	04/08/2003	Cleaving Process to Fabricate Multilayered Substrates Using Low Implantation Doses
7078317	USA	08/06/2004		Method and System for Source Switching and In-Situ Plasma Bonding
7094666	USA	01/24/2005		Method and System for Fabricating Strained Layers for the Manufacture of Integrated Circuits
7147709	USA	11/14/2003		Non-Contact Etch Annealing of Strained Layers Controlled Cleaving Process
7160790	USA	8/19/2003	1/9/2007	Thin Handle Substrate Method and Structure for Fabricating Devices Using One or More Films
7166520	USA	08/08/2005	06/24/2008	Provided by a Layer Transfer Process
7253081	USA	06/26/2001		Surface Finishing of SOI Substrates Usina an EPI Process
7348258	USA	08/06/2004	08/22/2006	Method and Device for Controlled Cleaving Process Thin Handle Substrate Method and Structure for Fabricating Devices Using One or More Films
7351644	USA	09/14/2006	06/24/2008	Provided by a Layer Transfer Process
7354815	USA	11/17/2004		Method for Fabricating Semiconductor Devices Using Strained Silicon Bearing Material
7371660	USA	11/16/2005	5/13/2008	Controlled Cleaving Process
7378330	USA	03/28/2006		Cleaving Process to Fabricate Multilayered Substrates Using Low Implantation Doses
7390724	USA	04/11/2005		Method and System for Lattice Space Engineering
7391047	USA	03/17/2006		Method and System for Fabricating Strained Layers for the Manufacture of Integrated Circuits A Method and Structure for Implanting Bonded Substrates for Electrical Conductivity
7399680 7410887	USA	01/26/2007		Controlled Process and Resulting Device
7427554	USA	08/12/2005		Manufacturing Strained Silicon Substrates Using a Backing Material
7462526	USA	06/09/2005		Method for Fabricating Semiconductor Devices Using Strained Silicon Bearing Material
7470600	USA	8/20/2007	12/30/2008	Method and Device for Controlled cleaving Process
7479441	USA	10/13/2006		Method and Apparatus for Flag-Less Wafer Bonding Tool
7547609	USA	11/15/2005		Method and Structure for Implanting Bonded Substrates for Electrical Conductivity
7595499	USA	02/19/2008	08/14/2012	Method and System for Fabricating Strained Layers for the Manufacture of Integrated Circuits Method and Structure for Fabricating Bonded Substrate Structures Using Thermal Processing to
7598153	USA	03/31/2006	08/10/2010	Remove Oxygen Species
7629666	USA	06/12/2008		Method and Structure for Implanting Bonded Substrates for Electrical Conductivity
	110.4	07/07/0005	00/00/0044	Method and Structure for Fabricating Multiple Tiled Regions onto a Plate Using a Controlled
7674687 7759217	USA	07/27/2005	03/22/2011 09/06/2011	Cleaving Process Controlled Process and Resulting Device
7759220	USA	04/05/2007		Method and Structure for Fabricating Solar Cells Using a Layer Transfer Processes
				Applications and Equipment of Substrate Stiffness Method and Resulting Devices for Layer Transfer
7772088	USA	02/24/2006	09/23/2008	
7776717	USA	08/20/2007	01/23/2007	Controlled Process and Resulting Device
7781305 7811900	USA USA	03/31/2008	04/01/2008	Controlled Cleaving Process Method and Structure for Fabricating Solar Cells Using a Thick Layer Transfer Process
7811900	USA	09/01/2007		Method and Structure for Fabricating Solar Cens Osing a Trick Layer Transfer Frocess
7811901	USA	12/01/2008	01/04/2007	Method and Edge Region Structure Using Co-Implanted Particles for Layer Transfer Processes
7846818	USA	07/10/2008		Controlled Process and Resulting Device
7863157	USA	03/13/2007		Method and Structure for Fabricating Solar Cells Using A Layer Transfer Process
7910456	USA	05/25/2007	11/19/2010	Liquid Based Substrate Method and Structure for Layer Transfer Applications Method and Structure Using Selected Implant Angles Using a Linear Accelerator Process for
7910458	USA	01/25/2008	10/06/2009	Manufacture of Free Standing Films of Materials
				Method and Structure for Fabricating Multiple Tiled Regions onto a Plate Using a Controlled
7911016	USA	01/27/2010		Cleaving Process
8012851 8012852	USA	03/24/2010 05/27/2010		Method and Structure for Fabricating Solar Cells Using A Layer Transfer Process Controlled Process and Resulting Device
8012852	USA	03/27/2010	04/24/2013	Method and Structure for Fabricating Multiple Tiled Regions onto a Plate Using a Controlled
8012855	USA	01/27/2010	04/10/2012	Cleaving Process
9071462	1104	01/27/2010	06/27/2012	Method and Structure for Fabricating Multiple Tiled Regions onto a Plate Using a Controlled
8071463 8110480	USA USA	03/23/2010		Cleaving Process Method and Structure for Fabricating Solar Cells Using a Thick Layer Transfer Process
8110480 8124499	USA	11/05/2007		Method and Structure for Thick Layer Transfer Using a Linear Accelerator
8133800	USA	07/23/2009		Free-Standing Thickness of Single Crystal Material and Method Having Carrier Lifetimes
8143165	USA	02/09/2009		Method for Fabricating Semiconductor Devices Using Strained Silicon Bearing Material
8,153,513	USA	07/24/2007		Method and System for Continuous Large-Area Scanning Implantation Process
8187377	USA	10/04/2002	05/04/2011	Non-Contact Etch Annealing of Strained Layers
8,222,119	USA	09/27/2011	03/22/2011	Apparatus and Method of Temperature Control During Cleaving Processes of Thick Film Materials
8,222,119 8241996	USA	02/24/2006	33/22/2011	Substrate Stiffness Method and Resulting Devices for Layer Transfer Process
	USA	07/24/2009	07/17/2012	Layer Transfer of Films Utilizing Controlled Propagation
8293619				
8293619 8329557	USA	05/12/2010	10/12/2010	Techniques for Forming Thin Films by Implantation with Reduced Channeling
	USA USA	07/29/2009		Race Track Configuration and Method for Wafering Silicon Solar Substrates
8329557	USA			

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Patent Number	Country	Filed	Issued	Title
8637382	USA	08/01/2011	05/31/2012	Layer Transfer of Films Utilizing Thermal Flux Regime For Energy Controlled Cleaving.
	Japan	03/16/2007	03/13/2012	Method and Structure for Fabricating Solar Cells
	EPO	05/07/2009	1/28/2014	Layer Transfer of Films Utilizing Controlled Shear Region
10-0810825	Korea (South)	01/10/2005	06/29/2012	An Apparatus and Method for Controlled Cleaving
				Method and Structure for Fabricating Bonded Substrate Structures Using Thermal Processing to
10-0996539	Korea (South)	01/19/2007	12/11/2012	Remove Oxygen Species
10-1154133	Korea (South)	08/31/2009	10/23/2012	Free-Standing Thickness of Single Crystal Material and Method Having Carrier Lifetimes
10-1163282	Korea (South)	08/25/2009	12/11/2012	Race Track Configuration and Method for Wafering Silicon Solar Substrates
ZL 200780022933.9	China	09/10/2007	12/03/2002	Method and Structure for Fabricating Solar Cells Using a Thick Layer Transfer Process
ZL 200810006997.6	China	01/28/2008	01/30/2001	Apparatus and Method of Temperature Control During Cleaving Processes of Thick Film Materials
ZL 200910138229.0	China	05/07/2009	11/11/2003	Layer Transfer of Films Utilizing Controlled Shear Region
ZL200580002085.6	China	01/10/2005	06/21/2005	An Apparatus and Method for Controlled Cleaving
ZL2006101629001.1	China	11/29/2006	11/27/2002	A Method and Structure for Implanting Bonded Substrates for Electrical Conductivity
ZL200680014752.7	China	02/24/2006	05/23/2008	Substrate Stiffness Method and Resulting Devices
ZL200780026734.5	China	07/25/2007	08/05/1997	Continuous Large-Area Scanning Implantation Process
ZL200780041135.0	China	11/06/2007	10/14/2003	Method and Structure for Thick Layer Transfer Using A Linear Accelerator
ZL200810009149.0	China	01/29/2008	01/15/2002	Method for Fabricating Free Standing Thickness of Materials Using One or More Semiconductor Substrates
ZL98804976.7	China	05/11/1998	08/31/1999	A Controlled Cleavage Process

In re

Silicon Genesis Corporation

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Debtor

SCHEDULE D - CREDITORS HOLDING SECURED CLAIMS

State the name, mailing address, including zip code, and last four digits of any account number of all entities holding claims secured by property of the debtor as of the date of filing of the petition. The complete account number of any account the debtor has with the creditor is useful to the trustee and the creditor and may be provided if the debtor chooses to do so. List creditors holding all types of secured interests such as judgment liens, gamishments, statutory liens, mortgages, deeds of trust, and other security interests.

other security interests. List creditors in alphabetical order to the extent practicable. If a minor child is a creditor, the child's initials and the name and address of the child's parent or guardian, such as "A.B., a minor child, by John Doe, guardian." Do not disclose the child's name. See, 11 U.S.C. §112 and Fed. R. Bankr. P. 1007(m). If all secured creditors will not fit on this page, use the continuation sheet provided. If any entity other than a spouse in a joint case may be jointly liable on a claim, place an "X" in the column labeled "Codebtor", include the entity on the appropriate schedule of creditors, and complete Schedule H - Codebtors. If a joint petition is filed, state whether the husband, wife, both of them, or the marital community may be liable on each claim by placing an "H", "W", "J", or "C" in the column labeled "Husband, Wife, Joint, or Community". If the claim is contingent, place an "X" in the column labeled "Contingent". If the claim is unliquidated, place an "X" in the column labeled "Unliquidated". If the claim is disputed, place an "X" in the column labeled "Disputed". (You may need to place an "X" in more than one of these three columns.) Total the columns labeled "Amount of Claim Without Deducting Value of Collateral" and "Unsecured Portion, if Any" in the boxes labeled "Total(s)" on the last sheet of the completed schedule. Report the total from the column labeled "Amount of Claim" also on the Summary of Schedules and, if the debtor is an individual with primarily consumer debts, report the total from the column labeled "Unsecured Portion" on the Statistical Summary of Certain Liabilities and Related Data. Check this box if debtor has no creditors holding secured claims to report on this Schedule D. Check this box if debtor has no creditors holding secured claims to report on this Schedule D.

CREDITOR'S NAME AND MAILING ADDRESS INCLUDING ZIP CODE, AND ACCOUNT NUMBER (See instructions above.)	CODEBTOR	н Н ¥ ⊃ С	sband, Wife, Joint, or Community DATE CLAIM WAS INCURRED, NATURE OF LIEN, AND DESCRIPTION AND VALUE OF PROPERTY SUBJECT TO LIEN	I N G F	PD-CD-LZC	D I S P U T E D	AMOUNT OF CLAIM WITHOUT DEDUCTING VALUE OF COLLATERAL	UNSECURED PORTION, IF ANY
Account No.			for notice purposes	Т	ATED			
Firsthand Capital Management, Inc, Agent 150 Almaden Blvd., Ste. 95113 San Jose, CA 95113		-			1	x		
			Value \$ 0.00				0.00	0.00
Account No.			11/03/2010					
Firsthand Technology Value Fund, Inc.			Non-Purchase Money Security accounts receivable and payment					
150 Almaden Blvd. Suite #1250		-	intangibles, equipment, intellectual			х		
San Jose, CA 95113							7 000 400 00	0.00
Account No.			Value \$ 16,411,872.00	\vdash			7,688,182.09	0.00
			Value \$					
Account No.								
			Value \$					
0 continuation sheets attached		L		ubto nis p			7,688,182.09	0.00
			(Report on Summary of Sc		ota 1le		7,688,182.09	0.00

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Silicon Genesis Corporation

Debtor

SCHEDULE E - CREDITORS HOLDING UNSECURED PRIORITY CLAIMS

A complete list of claims entitled to priority, listed separately by type of priority, is to be set forth on the sheets provided. Only holders of unsecured claims entitled to priority should be listed in this schedule. In the boxes provided on the attached sheets, state the name, mailing address, including zip code, and last four digits of the account number, if any, of all entities holding priority claims against the debtor or the property of the debtor, as of the date of the filing of the petition. Use a separate continuation sheet for each type of priority and label each with the type of priority.

The complete account number of any account the debtor has with the creditor is useful to the trustee and the creditor and may be provided if the debtor chooses to do so. If a minor child is a creditor, state the child's initials and the name and address of the child's parent or guardian, such as "A.B., a minor child, by John Doe, guardian." Do not disclose the child's name. See, 11 U.S.C. §112 and Fed. R. Bankr. P. 1007(m).

If any entity other than a spouse in a joint case may be jointly liable on a claim, place an "X" in the column labeled "Codebtor," include the entity on the appropriate schedule of creditors, and complete Schedule H-Codebtors. If a joint petition is filed, state whether the husband, wife, both of them, or the marital community may be liable on each claim by placing an "H," "W," "J," or "C" in the column labeled "Husband, Wife, Joint, or Community." If the claim is contingent, place an "X" in the column labeled "Contingent." If the claim is unliquidated, place an "X" in the column labeled "Unliquidated." If the claim is disputed, place an "X" in the column labeled "Disputed." (You may need to place an "X" in more than one of these three columns.)

Report the total of claims listed on each sheet in the box labeled "Subtotals" on each sheet. Report the total of all claims listed on this Schedule E in the box labeled "Total" on the last sheet of the completed schedule. Report this total also on the Summary of Schedules.

Report the total of amounts entitled to priority listed on each sheet in the box labeled "Subtotals" on each sheet. Report the total of all amounts entitled to priority listed on this Schedule E in the box labeled "Totals" on the last sheet of the completed schedule. Individual debtors with primarily consumer debts report this total also on the Statistical Summary of Certain Liabilities and Related Data.

Report the total of amounts not entitled to priority listed on each sheet in the box labeled "Subtotals" on each sheet. Report the total of all amounts not entitled to priority listed on this Schedule E in the box labeled "Totals" on the last sheet of the completed schedule. Individual debtors with primarily consumer debts report this total also on the Statistical Summary of Certain Liabilities and Related Data.

Check this box if debtor has no creditors holding unsecured priority claims to report on this Schedule E.

TYPES OF PRIORITY CLAIMS (Check the appropriate box(es) below if claims in that category are listed on the attached sheets)

□ Domestic support obligations

Claims for domestic support that are owed to or recoverable by a spouse, former spouse, or child of the debtor, or the parent, legal guardian, or responsible relative of such a child, or a governmental unit to whom such a domestic support claim has been assigned to the extent provided in 11 U.S.C. § 507(a)(1).

Extensions of credit in an involuntary case

Claims arising in the ordinary course of the debtor's business or financial affairs after the commencement of the case but before the earlier of the appointment of a trustee or the order for relief. 11 U.S.C. § 507(a)(3).

□ Wages, salaries, and commissions

Wages, salaries, and commissions, including vacation, severance, and sick leave pay owing to employees and commissions owing to qualifying independent sales representatives up to \$12,475* per person earned within 180 days immediately preceding the filing of the original petition, or the cessation of business, whichever occurred first, to the extent provided in 11 U.S.C. § 507(a)(4).

Contributions to employee benefit plans

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Money owed to employee benefit plans for services rendered within 180 days immediately preceding the filing of the original petition, or the cessation of business, whichever occurred first, to the extent provided in 11 U.S.C. § 507(a)(5).

□ Certain farmers and fishermen

Claims of certain farmers and fishermen, up to \$6,150* per farmer or fisherman, against the debtor, as provided in 11 U.S.C. § 507(a)(6).

Deposits by individuals

Claims of individuals up to \$2,775* for deposits for the purchase, lease, or rental of property or services for personal, family, or household use, that were not delivered or provided. 11 U.S.C. § 507(a)(7).

Taxes and certain other debts owed to governmental units

Taxes, customs duties, and penalties owing to federal, state, and local governmental units as set forth in 11 U.S.C. § 507(a)(8).

□ Commitments to maintain the capital of an insured depository institution

Claims based on commitments to the FDIC, RTC, Director of the Office of Thrift Supervision, Comptroller of the Currency, or Board of Governors of the Federal Reserve System, or their predecessors or successors, to maintain the capital of an insured depository institution. 11 U.S.C. § 507 (a)(9).

□ Claims for death or personal injury while debtor was intoxicated

Claims for death or personal injury resulting from the operation of a motor vehicle or vessel while the debtor was intoxicated from using alcohol, a drug, or another substance. 11 U.S.C. § 507(a)(10).

* Amount subject to adjustment on 4/01/16, and every three years thereafter with respect to cases commenced on or after the date of adjustment.

continuation sheets attached 02/18/15 Entered: 02/18/15 17:43:37 Page 15 of Doc#8 25

st Case Bankruptcy

Case No. 15-50525 MEH

Debtor

SCHEDULE E - CREDITORS HOLDING UNSECURED PRIORITY CLAIMS (Continuation Sheet)

Taxes and Certain Other Debts Owed to Governmental Units

							TYPE OF PRIORITY	7
CREDITOR'S NAME, AND MAILING ADDRESS INCLUDING ZIP CODE, AND ACCOUNT NUMBER (See instructions.)	C O D E B T O R	Hu H W J C	sband, Wife, Joint, or Community DATE CLAIM WAS INCURRED AND CONSIDERATION FOR CLAIM	CONTINGEN	UNLLQULDA	E	AMOUNT OF CLAIM	AMOUNT NOT ENTITLED TO PRIORITY, IF ANY AMOUNT ENTITLED TO PRIORITY
Account No. 97-329546				Т	D A T E D			
California State Board of Equalization PO Box 942879 Sacramento, CA 94279-0001		-						0.00
Account No.							186.00	186.00
Tax Collector, Santa Clara County 70 West Hedding St. East Wing, 6th Flr San Jose, CA 95110-1767		-						Unknown
							Unknown	Unknown
Account No.								
Account No.								
Account No.								
Sheet <u>1</u> of <u>1</u> continuation sheets atta	che	d te		Subt	ota	ı ıl		0.00
Schedule of Creditors Holding Unsecured Price				this	pag	ge)	186.00	186.00
			(Report on Summary of S		'ota lule		186.00	0.00 186.00
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Debtor

SCHEDULE F - CREDITORS HOLDING UNSECURED NONPRIORITY CLAIMS

State the name, mailing address, including zip code, and last four digits of any account number, of all entities holding unsecured claims without priority against the debtor or the property of the debtor, as of the date of filing of the petition. The complete account number of any account the debtor has with the creditor is useful to the trustee and the creditor and may be provided if the debtor chooses to do so. If a minor child is a creditor, state the child's initials and the name and address of the child's parent or guardian, such as "A.B., a minor child, by John Doe, guardian." Do not disclose the child's name. See, 11 U.S.C. §112 and Fed. R. Bankr. P. 1007(m). Do not include claims listed in Schedules D and E. If all creditors will not fit on this page, use the continuation sheet provided.

If any entity other than a spouse in a joint case may be jointly liable on a claim, place an "X" in the column labeled "Codebtor," include the entity on the appropriate schedule of creditors, and complete Schedule H - Codebtors. If a joint petition is filed, state whether the husband, wife, both of them, or the marital community may be liable on each claim by placing an "H," "W," "J," or "C" in the column labeled "Husband, Wife, Joint, or Community."

If the claim is contingent, place an "X" in the column labeled "Contingent." If the claim is unliquidated, place an "X" in the column labeled "Unliquidated." If the claim is disputed, place an "X" in the column labeled "Disputed." (You may need to place an "X" in more than one of these three columns.)

Report the total of all claims listed on this schedule in the box labeled "Total" on the last sheet of the completed schedule. Report this total also on the Summary of Schedules and, if the debtor is an individual with primarily consumer debts, report this total also on the Statistical Summary of Certain Liabilities and Related Data.

□ Check this box if debtor has no creditors holding unsecured claims to report on this Schedule F.

CREDITOR'S NAME, MAILING ADDRESS INCLUDING ZIP CODE, AND ACCOUNT NUMBER (See instructions above.)	C O D E B T O R		Husband, Wife, Joint, or Community H DATE CLAIM WAS INCURRED AND CONSIDERATION FOR CLAIM. IF CLAIM IS SUBJECT TO SETOFF, SO STATE.	CONTINGEN	QU	T	AMOUNT OF CLAIM
Account No.				T	D A T E D		
1800flowers (VISA)		-					
							0.00
Account No.							
ACIP International, Inc (PATENT) 1280 Boulevard Way, Suite# 202 Walnut Creek, CA 94595		-					
Account No.							956.20
Air Products & Chemicals, Inc. P.O Box# 935430 Atlanta, GA 31193-5430		-					
							2,210.89
Account No.	_						
Airgas USA, LLC. P.O Box# 7423 Pasadena, CA 91109-7423		-					
							93.54
_ 5 continuation sheets attached		1	(Total of	Sub this			3,260.63

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Debtor

SCHEDULE F - CREDITORS HOLDING UNSECURED NONPRIORITY CLAIMS (Continuation Sheet)

P.O. Box 7794 San Francisco, CA 94120		-					
Account No. Datasafe, Inc							
Beijing East IP Ltd. (PATENT) Tower E2, The Towers Oriental Plaza No. East Chang An Ave. Suite# 1601, Dongchen District Beijing, P. 100738		-					1,575.59
Account No.						$\left \right $	
Account No. AT&T Ethernet P.O. Box# 5019 Carol Stream, IL 60197-5019		-					4,034.12
Account No.							69.01
AT&T - fka SBC/Pacific Bell P.O. Box# 5025 Carol Stream, IL 60197-5025		-					
Account No.							35,807.23
Alston & Bird, LLP (Law Firm) P.O Box# 933124 Atlanta, GA 31193-3124		-			D		
Account No.		\vdash		- Ñ T	A T E	ľ	
CREDITOR'S NAME, MAILING ADDRESS INCLUDING ZIP CODE, AND ACCOUNT NUMBER (See instructions above.)	C O D E B T O R	Hu H V J C	ISBAND, Wife, Joint, or Community DATE CLAIM WAS INCURRED AND CONSIDERATION FOR CLAIM. IF CLAIM IS SUBJECT TO SETOFF, SO STATE.	CONTINGEN	UNL-QU-D	D I S P UT E D	AMOUNT OF CLAIN

Case No. 15-50525 MEH

Debtor

SCHEDULE F - CREDITORS HOLDING UNSECURED NONPRIORITY CLAIMS (Continuation Sheet)

		ц.,	sband, Wife, Joint, or Community	C	U	D	
CREDITOR'S NAME, MAILING ADDRESS INCLUDING ZIP CODE, AND ACCOUNT NUMBER (See instructions above.)	C O D E B T O R	H U H	DATE CLAIM WAS INCURRED AND CONSIDERATION FOR CLAIM. IF CLAIM IS SUBJECT TO SETOFF, SO STATE.	CONT-NGEN	ONL I QU I DATE	I S P U T E D	AMOUNT OF CLAIM
Account No.				Т	T E D		
Federal Express P.O. Box 7221 Pasadena, CA 91109-7321		-			D		161.75
Account No.							101.75
GE Mobile Water, Inc. P.O. Box# 742132 Los Angeles, CA 90074-2132		-					
Account No.							169.66
Home Depot, The Home Depot Credit Services Dept. 32-2501 P.O. Box# 9055 Des Moines, IA 50368-9055		-					556.19
Account No.			11/18/2014				
J.D. Molex One, LLC 1484 Saratoga Ave. Saratoga, CA 95070		-	restoration of former business premises		x		
Account No.							180,000.00
JB Precision, Inc. 1640 Dell Ave. Campbell, CA 95008		-					1,763.54
Sheet no. 2 of 5 sheets attached to Schedule of Creditors Holding Unsecured Nonpriority Claims		1	r (Total of t	Sub his			182,651.14

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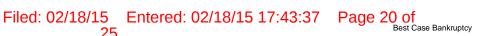
Case No. 15-50525 MEH

Debtor

SCHEDULE F - CREDITORS HOLDING UNSECURED NONPRIORITY CLAIMS (Continuation Sheet)

CREDITOR'S NAME,	С	Hu	isband, Wife, Joint, or Community	c	U	D	
MAILING ADDRESS INCLUDING ZIP CODE, AND ACCOUNT NUMBER (See instructions above.)	CODEBTOR	C M H	DATE CLAIM WAS INCURRED AND CONSIDERATION FOR CLAIM. IF CLAIM IS SUBJECT TO SETOFF, SO STATE.	CONTINGENT		D I S P UT E D	AMOUNT OF CLAIM
Account No.				Т	E		
Landauer, Inc. P.O Box 809051 Chicago, IL 60680-9051		-			D		220.00
Account No.						\vdash	326.90
Mathys & Squire LLP (PATENT) 32 London Bridge Street London SE1 9SG, Un		-					
							2,285.71
Account No.							
Oh, Back & Hahm (Patents- Korea) 996-14 Deachidong Kangnamgu 4th. Fl. HANA Bldg. Seoul, Re 135-502		-					1,546.31
Account No.	╉					┢	
PG&E P.O. Box 997300 Sacramento, CA 95899-7300		-					1,087.53
Account No.	╉	\vdash		-	╞	\vdash	1,007.33
Pitney Bowes Global Financial Svcs, LLC PO Box# 371887 Pittsburgh, PA 15250-7887		-					32.00
Sheet no. <u>3</u> of <u>5</u> sheets attached to Schedule of	f	<u> </u>		Sub	L tot∘	1 1	
Creditors Holding Unsecured Nonpriority Claims	L		(Total of				5,278.45

Creditors Holding Unsecured Nonpriority Claims



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Debtor

SCHEDULE F - CREDITORS HOLDING UNSECURED NONPRIORITY CLAIMS (Continuation Sheet)

	С	н	usband, Wife, Joint, or Community	С	U	D	
CREDITOR'S NAME, MAILING ADDRESS INCLUDING ZIP CODE, AND ACCOUNT NUMBER (See instructions above.)	CODEBTOR	H W J		CONTINUE	L Q U	S P U T E	AMOUNT OF CLAIM
Account No.				Т	D A T E D		
Pitney Bowes Postage by Phone P.O Box# 371874 Pittsburgh, PA 15250-7874		-					50.00
Account No.	╉			+		┢	50.00
Republic Services, Inc. Republic Svcs of Santa Clara County P.O Box# 78829 Phoenix, AZ 85062-8829		-					
Account No.	┥						3,451.14
Shred Works, Inc. Dept# 34654 P.O Box# 3900 San Francisco, CA 94139		-					261.00
Account No.						+	
Stearn Research Center Owner's Association 7917 Winged Foot Court Pleasanton, CA 94588		-					4,182.62
Account No.					+	+	.,
U.S. Bank / Visa Business Account PO Box 790408 St. Louis, MO 63179-0408		-					142.76
Sheet no4 of _5 sheets attached to Schedule of		<u> </u>	1	Sub	tot	 al	
Creditors Holding Unsecured Nonpriority Claims			(Total o				8,087.52

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Case No. 15-50525 MEH

Debtor

SCHEDULE F - CREDITORS HOLDING UNSECURED NONPRIORITY CLAIMS (Continuation Sheet)

Husband, Wife, Joint, or Community UNLIQUIDATED CODEBTOR DISPUTED CONTINGENT CREDITOR'S NAME, MAILING ADDRESS н DATE CLAIM WAS INCURRED AND INCLUDING ZIP CODE. W CONSIDERATION FOR CLAIM. IF CLAIM AND ACCOUNT NUMBER J AMOUNT OF CLAIM IS SUBJECT TO SETOFF, SO STATE. С (See instructions above.) Account No. W2 Systems **106 Cresta Vista Drive** San Francisco, CA 94127 8,557.94 Account No. Wilson Gunn Central Court 25 Southampton Bld. London, England WC2A 1AL 877.73 Account No. 00100000029015 **XO Communications** File 50550 Los Angeles, CA 90074-0550 20.25 Account No. Yamakawa International Patent Office Shuwa-Tameike Bldg # 4-2 Nagatacho 2, Chiyodaku, Tokyo, JAPAN 11,272.36 Account No. Sheet no. 5 of 5 sheets attached to Schedule of Subtotal 20,728.28 Creditors Holding Unsecured Nonpriority Claims (Total of this page) Total 262,675.10

(Report on Summary of Schedules)

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In re

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Silicon Genesis Corporation

Debtor

SCHEDULE G - EXECUTORY CONTRACTS AND UNEXPIRED LEASES

Describe all executory contracts of any nature and all unexpired leases of real or personal property. Include any timeshare interests. State nature of debtor's interest in contract, i.e., "Purchaser", "Agent", etc. State whether debtor is the lessor or lessee of a lease. Provide the names and complete mailing addresses of all other parties to each lease or contract described. If a minor child is a party to one of the leases or contracts, state the child's initials and the name and address of the child's parent or guardian, such as "A.B., a minor child, by John Doe, guardian." Do not disclose the child's name. See, 11 U.S.C. §112 and Fed. R. Bankr. P. 1007(m). Check this box if debtor has no executory contracts or unexpired leases.

Name and Mailing Address, Including Zip Code, of Other Parties to Lease or Contract	Description of Contract or Lease and Nature of Debtor's Interest. State whether lease is for nonresidential real property. State contract number of any government contract.	
Alexander Meyer, Senior Director, New Business Development Applied Materials, Inc. 3050 Bowers Avenue, M/S 1954 Santa Clara, CA 95054	[05/29/2003] Outbound lease of intellectual property	
Applied Materials, Inc. 3050 Bowers Avenue Attn: Jim Pursiano Santa Clara, CA 95054	[04/30/1999] Outbound lease of intellectual property	
Applied Materials, Inc. 2881 Scott Blvd., M/S 2064 Attn: Joseph Sweeney, VP, Legal Affairs & Intellectual Property Santa Clara, CA 95054	[05-29-2003] Outbound lease of intellectual property	
EV Group E. Thallner GmbH DI Erich Thallner Strasse 1 Attn: Dr. Peter Podesser A-4782 St. Florian am Inn, Austria	[10/28/2003] Outbound lease of intellectual property	
QMAT, Inc. Attn: Francois Henley, President & CEO 2424 Walsh Avenue Santa Clara, CA 95051-1303	[12/13/2012] Outbound lease of intellectual property 1/1/2015 - at will cost share agreement pursuant to which SiGen sharer R&D and admin space at 2424 Walsh Ave., Santa Clara, CA 95051	
Shin-Etsu Chemical Co., Ltd. 6-1, Ohtemachi 2-chome Chiyoda-ku, Tokyo 100-0004	[06/09/2005] Outbound lease of intellectual property	
SunEdison, Inc. f/k/a MEMC Electronic Materials, Inc. 501 Pearl Drive Saint Peters, MO 63376	[0701/2014] Outbound lease of intellectual property	

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In re Silicon Genesis Corporation Case No. 15-50525 MEH

Debtor

SCHEDULE H - CODEBTORS

Provide the information requested concerning any person or entity, other than a spouse in a joint case, that is also liable on any debts listed by debtor in the schedules of creditors. Include all guarantors and co-signers. If the debtor resides or resided in a community property state, commonwealth, or territory (including Alaska, Arizona, California, Idaho, Louisiana, Nevada, New Mexico, Puerto Rico, Texas, Washington, or Wisconsin) within the eight year period immediately preceding the commencement of the case, identify the name of the debtor's spouse and of any former spouse who resides or resided with the debtor in the community property state, commonwealth, or territory. Include all names used by the nondebtor spouse during the eight years immediately preceding the commencement of this case. If a minor child is a codebtor or a creditor, state the child's initials and the name and address of the child's parent or guardian, such as "A.B., a minor child, by John Doe, guardian." Do not disclose the child's name. See, 11 U.S.C. §112 and Fed. R. Bankr. P. 1007(m).

Check this box if debtor has no codebtors.

NAME AND ADDRESS OF CODEBTOR

NAME AND ADDRESS OF CREDITOR

United States Bankruptcy Court Northern District of California

Debtor(s)

In re Silicon Genesis Corporation

Case No. 15-Chapter 11

. <u>15-50525 MEH</u>

DECLARATION CONCERNING DEBTOR'S SCHEDULES

DECLARATION UNDER PENALTY OF PERJURY ON BEHALF OF CORPORATION OR PARTNERSHIP

I, the President and CEO of the corporation named as debtor in this case, declare under penalty of perjury that I have read the foregoing summary and schedules, consisting of 24 sheets, and that they are true and correct to the best of my knowledge, information, and belief.

Date February 18, 2015

Signature /s/ Theodore E. Fong Theodore E. Fong President and CEO

Penalty for making a false statement or concealing property: Fine of up to \$500,000 or imprisonment for up to 5 years or both. 18 U.S.C. §§ 152 and 3571.